

NOT RECOMMENDED FOR NEW DESIGN **USE DMN2058U**



DMG3420U

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	29m $Ω$ @ V _{GS} = 10 V	6.5A
20V	35mΩ @ V _{GS} = 4.5 V	5.2A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

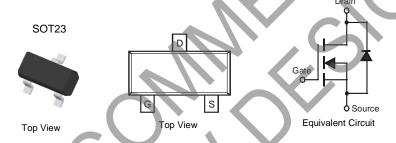
- General Purpose Interfacing Switch
- **Power Management Functions**

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



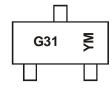
Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMG3420U-7	Standard	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4.. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



G31 = Product Type Marking Code YM or $\overline{Y}M$ = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2009	~	2019	2020	202	21 20)22 2	2023	2024	2025	2026	2027
Code	W	?	G	Н			J	K	L	M	N	0
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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Characte	eristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±12	V	
Continuous Drain Current (Note 5)	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I _D	5.47 3.43	А	
Pulsed Drain Current (Note 6)			I _{DM}	20	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.74	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{\theta JA}$	167	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

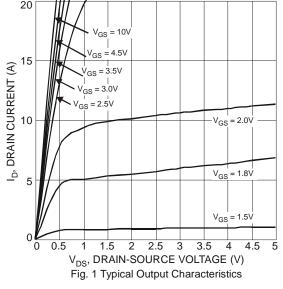
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

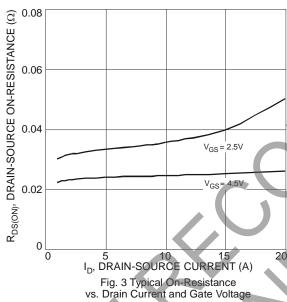
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20			V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	47	_	1.0	μA	$V_{DS} = 20V$, $V_{GS} = 0V$	
Gate-Source Leakage	Igss	13		±100	nΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.5	0.95	1.2	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
			21	29		$V_{GS} = 10V, I_D = 6A$	
Statia Drain Course On Registenes			25	35	0	$V_{GS} = 4.5V, I_D = 5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	/	34	48	mΩ	V _{GS} = 2.5V, I _D = 4A	
			65	91		V _{GS} = 1.8V, I _D = 2A	
Forward Transfer Admittance	Y _{fs}	/- ,	9	_	s	$V_{DS} = 5V, I_D = 3.8A$	
Diode Forward Voltage	V _{SD}		0.75	1.0	V	V _{GS} = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		434.7	1	pF		
Output Capacitance	Coss	_	69.1	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	61.2	_	pF	1 = 1.0WH12	
Gate Resistance	Rg	_	1.53	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_g	_	5.4	_	nC		
Gate-Source Charge	Q _{gs}	_	0.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Q_{gd}	_	1.5	_	nC	$I_D = 6A$	
Turn-On Delay Time	t _{D(ON)}	_	6.5	_	ns		
Turn-On Rise Time	t _R	_	8.3	_	ns	$V_{DD} = 10V, V_{GS} = 5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	21.6	_	ns	$R_L = 1.7\Omega$, $R_g = 6\Omega$	
Turn-Off Fall Time	t _F	_	5.3	_	ns		

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.







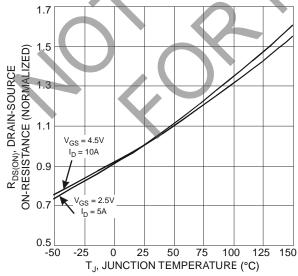
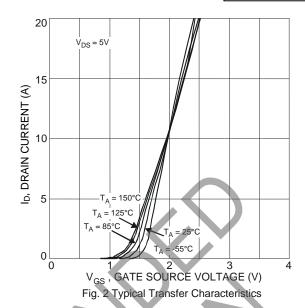
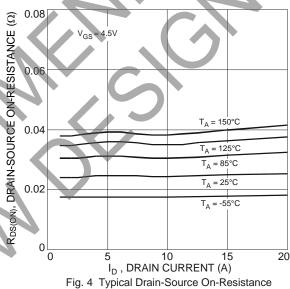


Fig. 5 On-Resistance Variation with Temperature





vs. Drain Current and Temperature

0.06 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.05 0.04 $V_{GS} = 2.5V$ I_D = 5A 0.03 $V_{GS} = 4.5V$ 0.02 $I_D = 10A$ 0.01 0 -50 50 100 125 -25 25 75 T_J, JUNCTION TEMPERATURE (°C)



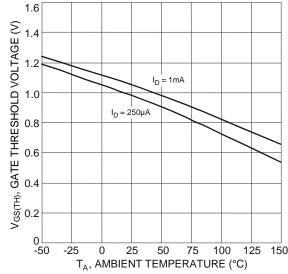
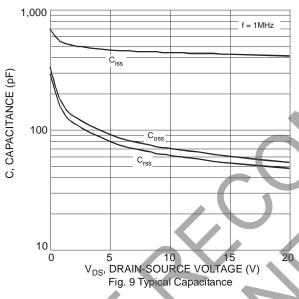
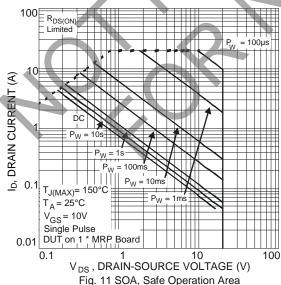
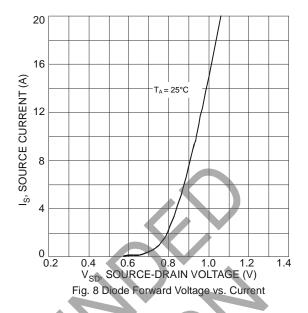
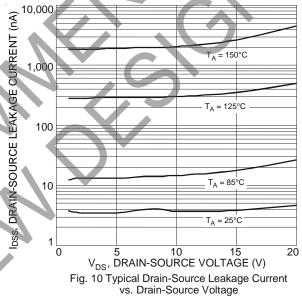


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

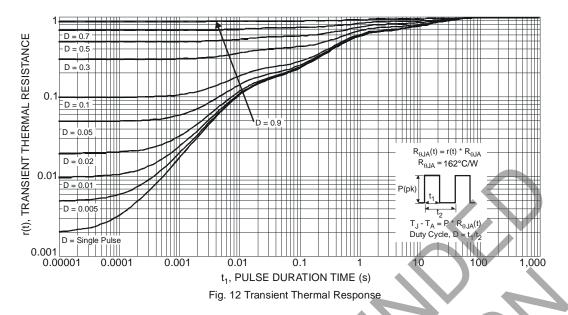






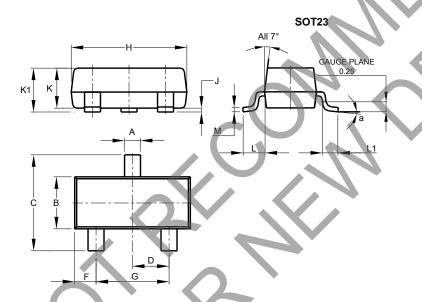






Package Outline Dimensions

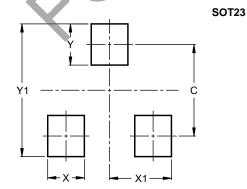
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Y	0.9			
Y1	2.9			



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